**TENTATIVE** TOSHIBA MOS DIGITAL INTEGRATED CIRCUIT SILICON GATE CMOS

# 262,144-WORD BY 16-BIT FULL CMOS STATIC RAM

## DESCRIPTION

The TC55NEM216AFTN is a 4,194,304-bit static random access memory (SRAM) organized as 262,144 words by 16 bits. Fabricated using Toshiba's CMOS Silicon gate process technology, this device operates from a single 5V ± 10% power supply. Advanced circuit technology provides both high speed and low power at an operating current of 3 mA/MHz (typ) and a minimum cycle time of 55 ns. It is automatically placed in low-power mode at 1 μA standby current (typ) when chip enable ($\overline{CE}$) is asserted high. There are two control inputs. $\overline{CE}$ is used to select the device and for data retention control, and output enable ($\overline{OE}$) provides fast memory access. Data byte control pin ($\overline{LB}$, $\overline{UB}$) provides lower and upper byte access. This device is well suited to various microprocessor system applications where high speed, low power and battery backup are required. And, with a guaranteed operating extreme temperature range of −40° to 85°C, the TC55NEM216AFTN can be used in environments exhibiting extreme temperature conditions. The TC55NEM216AFTN is available in a plastic 54-pin thin-small-outline package (TSOP).

## FEATURES

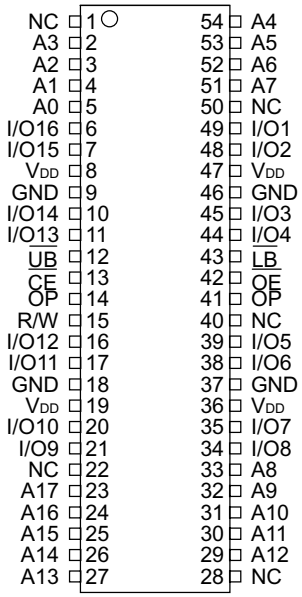
- Low-power dissipation
  Operating: 15 mW/MHz (typical)
- Single power supply voltage of 5 V ± 10%
- Power down features using $\overline{CE}$
- Data retention supply voltage of 2.0 to 5.5 V
- Direct TTL compatibility for all inputs and outputs
- Wide operating temperature range of −40° to 85°C
- Standby Current (maximum): 20 μA
- Access Times (maximum):

| | TC55NEM216AFTN | |
|---|---|---|
| | 55 | 70 |
| Access Time | 55 ns | 70 ns |
| $\overline{CE}$ Access Time | 55 ns | 70 ns |
| $\overline{OE}$ Access Time | 30 ns | 35 ns |

- Package:
  TSOP II54-P-400-0.80 (Weight: g typ)

## PIN ASSIGNMENT (TOP VIEW)

54 PIN TSOP

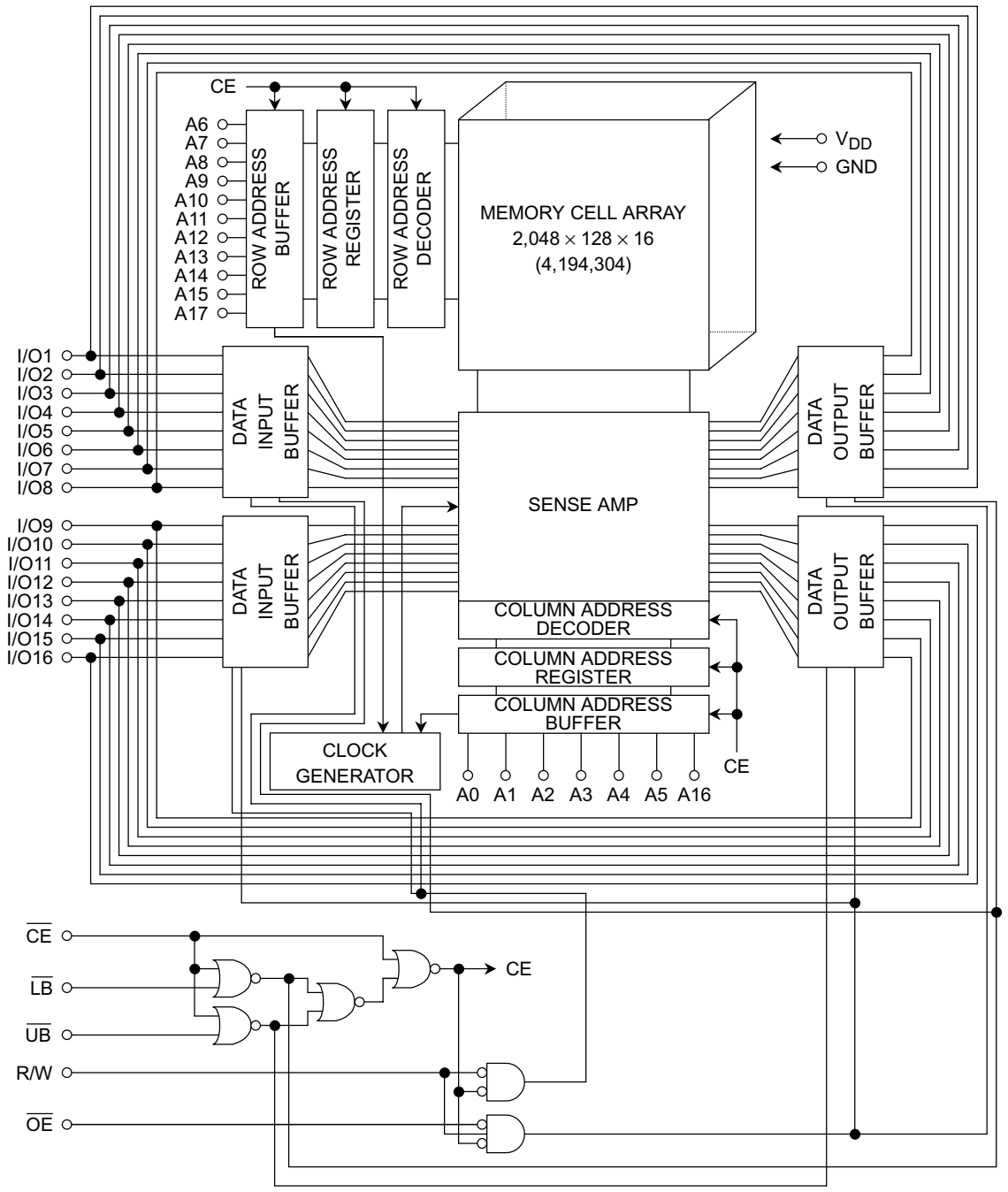



## PIN NAMES

| | |
|---|---|
| A0~A17 | Address Inputs |
| $\overline{CE}$ | Chip Enable |
| R/W | Read/Write Control |
| $\overline{OE}$ | Output Enable |
| $\overline{LB}$, $\overline{UB}$ | Data Byte Control |
| I/O1~I/O16 | Data Inputs/Outputs |
| $V_{DD}$ | Power (+5 V) |
| GND | Ground |
| NC | No Connection |
| OP* | Option |

*: OP pin must be open or connected to GND.

## BLOCK DIAGRAM



## OPERATING MODE

| MODE | $\overline{CE}$ | $\overline{OE}$ | R/W | $\overline{LB}$ | $\overline{UB}$ | I/O1~I/O8 | I/O9~I/O16 | POWER |
|---|---|---|---|---|---|---|---|---|
| Read | L | L | H | L | L | Output | Output | $I_{DDO}$ |
| | L | L | H | H | L | High-Z | Output | $I_{DDO}$ |
| | L | L | H | L | H | Output | High-Z | $I_{DDO}$ |
| Write | L | * | L | L | L | Input | Input | $I_{DDO}$ |
| | L | * | L | H | L | High-Z | Input | $I_{DDO}$ |
| | L | * | L | L | H | Input | High-Z | $I_{DDO}$ |
| Output Deselect | L | H | H | L | L | High-Z | High-Z | $I_{DDO}$ |
| | L | H | H | H | L | High-Z | High-Z | $I_{DDO}$ |
| | L | H | H | L | H | High-Z | High-Z | $I_{DDO}$ |
| Standby | H | * | * | * | * | High-Z | High-Z | $I_{DDS}$ |
| | * | * | * | H | H | High-Z | High-Z | $I_{DDS}$ |

* = don't care
H = logic high
L = logic low

## MAXIMUM RATINGS

| SYMBOL | RATING | VALUE | UNIT |
|---|---|---|---|
| $V_{DD}$ | Power Supply Voltage | −0.3~7.0 | V |
| $V_{IN}$ | Input Voltage | −0.3*~7.0 | V |
| $V_{I/O}$ | Input/Output Voltage | −0.5~$V_{DD}$ + 0.5 | V |
| $P_D$ | Power Dissipation | 0.6 | W |
| $T_{solder}$ | Soldering Temperature (10s) | 260 | °C |
| $T_{stg}$ | Storage Temperature | −55~150 | °C |
| $T_{opr}$ | Operating Temperature | −40~85 | °C |

*: −2.0 V when measured at a pulse width of 20ns

## DC RECOMMENDED OPERATING CONDITIONS (Ta = −40° to 85°C)

| SYMBOL | PARAMETER | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|
| $V_{DD}$ | Power Supply Voltage | 4.5 | 5.0 | 5.5 | V |
| $V_{IH}$ | Input High Voltage | 2.2 | — | $V_{DD}$ + 0.3 | V |
| $V_{IL}$ | Input Low Voltage | −0.3* | — | 0.6 | V |
| $V_{DH}$ | Data Retention Supply Voltage | 2.0 | — | 5.5 | V |

*: −2.0 V when measured at a pulse width of 20ns

## DC CHARACTERISTICS (Ta = –40° to 85°C, $V_{DD}$ = 5 V ± 10%)

| SYMBOL | PARAMETER | TEST CONDITION | | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|---|
| $I_{IL}$ | Input Leakage Current | $V_{IN}$ = 0 V~$V_{DD}$ | | | — | — | ±1.0 | μA |
| $I_{OH}$ | Output High Current | $V_{OH}$ = 2.4 V | | | –1.0 | — | — | mA |
| $I_{OL}$ | Output Low Current | $V_{OL}$ = 0.4 V | | | 2.1 | — | — | mA |
| $I_{LO}$ | Output Leakage Current | $\overline{CE}$ = $V_{IH}$ or $\overline{LB}$ = $\overline{UB}$ = $V_{IH}$ or R/W = $V_{IL}$ or $\overline{OE}$ = $V_{IH}$, $V_{OUT}$ = 0 V~$V_{DD}$ | | | — | — | ±1.0 | μA |
| $I_{DDO1}$ | Operating Current | $\overline{CE}$ = $V_{IL}$ and R/W = $V_{IH}$, $\overline{LB}$ = $\overline{UB}$ = $V_{IL}$, $I_{OUT}$ = 0 mA, Other Input = $V_{IH}/V_{IL}$ | $t_{cycle}$ | MIN | — | — | 35 | mA |
| | | | | 1 μs | — | 8 | — | |
| $I_{DDO2}$ | | $\overline{CE}$ = 0.2 V and R/W = $V_{DD}$ – 0.2 V, $\overline{LB}$ = $\overline{UB}$ = 0.2 V, $I_{OUT}$ = 0 mA, Other Input = $V_{DD}$ – 0.2 V/0.2 V | $t_{cycle}$ | MIN | — | — | 30 | mA |
| | | | | 1 μs | — | 3 | — | |
| $I_{DDS1}$ | Standby Current | 1) $\overline{CE}$ = $V_{IH}$ 2) $\overline{LB}$ = $\overline{UB}$ = $V_{IH}$ | | | — | — | 3 | mA |
| $I_{DDS2}$ | | 1) $\overline{CE}$ = $V_{DD}$ – 0.2 V 2) $\overline{LB}$ = $\overline{UB}$ = $V_{DD}$ – 0.2 V, $\overline{CE}$ = 0.2 V | Ta = 25°C | | — | 1 | — | μA |
| | | | Ta = –40~40°C | | — | — | 3 | |
| | | | Ta = –40~85°C | | — | — | 20 | |

## CAPACITANCE (Ta = 25°C, f = 1 MHz)

| SYMBOL | PARAMETER | TEST CONDITION | MAX | UNIT |
|---|---|---|---|---|
| $C_{IN}$ | Input Capacitance | $V_{IN}$ = GND | 10 | pF |
| $C_{OUT}$ | Output Capacitance | $V_{OUT}$ = GND | 10 | pF |

Note: This parameter is periodically sampled and is not 100% tested.

## AC CHARACTERISTICS AND OPERATING CONDITIONS

**(Ta = –40° to 85°C, $V_{DD}$ = 5 V ± 10%)**

READ CYCLE

| SYMBOL | PARAMETER | TC55NEM216AFTN | | | | UNIT |
|---|---|---|---|---|---|---|
| | | 55 | | 70 | | |
| | | MIN | MAX | MIN | MAX | |
| $t_{RC}$ | Read Cycle Time | 55 | — | 70 | — | ns |
| $t_{ACC}$ | Address Access Time | — | 55 | — | 70 | |
| $t_{CO}$ | Chip Enable Access Time | — | 55 | — | 70 | |
| $t_{OE}$ | Output Enable Access Time | — | 30 | — | 35 | |
| $t_{BA}$ | Data Byte Control Access Time | — | 55 | — | 70 | |
| $t_{COE}$ | Chip Enable Low to Output Active | 5 | — | 5 | — | |
| $t_{OEE}$ | Output Enable Low to Output Active | 0 | — | 0 | — | |
| $t_{BE}$ | Data Byte Control Low to Output Active | 5 | — | 5 | — | |
| $t_{OD}$ | Chip Enable High to Output High-Z | — | 25 | — | 30 | |
| $t_{ODO}$ | Output Enable High to Output High-Z | — | 25 | — | 30 | |
| $t_{BD}$ | Data Byte Control High to Output High-Z | — | 25 | — | 30 | |
| $t_{OH}$ | Output Data Hold Time | 10 | — | 10 | — | |

WRITE CYCLE

| SYMBOL | PARAMETER | TC55NEM216AFTN | | | | UNIT |
|---|---|---|---|---|---|---|
| | | 55 | | 70 | | |
| | | MIN | MAX | MIN | MAX | |
| $t_{WC}$ | Write Cycle Time | 55 | — | 70 | — | ns |
| $t_{WP}$ | Write Pulse Width | 40 | — | 50 | — | |
| $t_{CW}$ | Chip Enable to End of Write | 45 | — | 55 | — | |
| $t_{BW}$ | Data Byte Control to End of Write | 45 | — | 55 | — | |
| $t_{AS}$ | Address Setup Time | 0 | — | 0 | — | |
| $t_{WR}$ | Write Recovery Time | 0 | — | 0 | — | |
| $t_{ODW}$ | R/W Low to Output High-Z | — | 25 | — | 30 | |
| $t_{OEW}$ | R/W High to Output Active | 0 | — | 0 | — | |
| $t_{DS}$ | Data Setup Time | 25 | — | 30 | — | |
| $t_{DH}$ | Data Hold Time | 0 | — | 0 | — | |

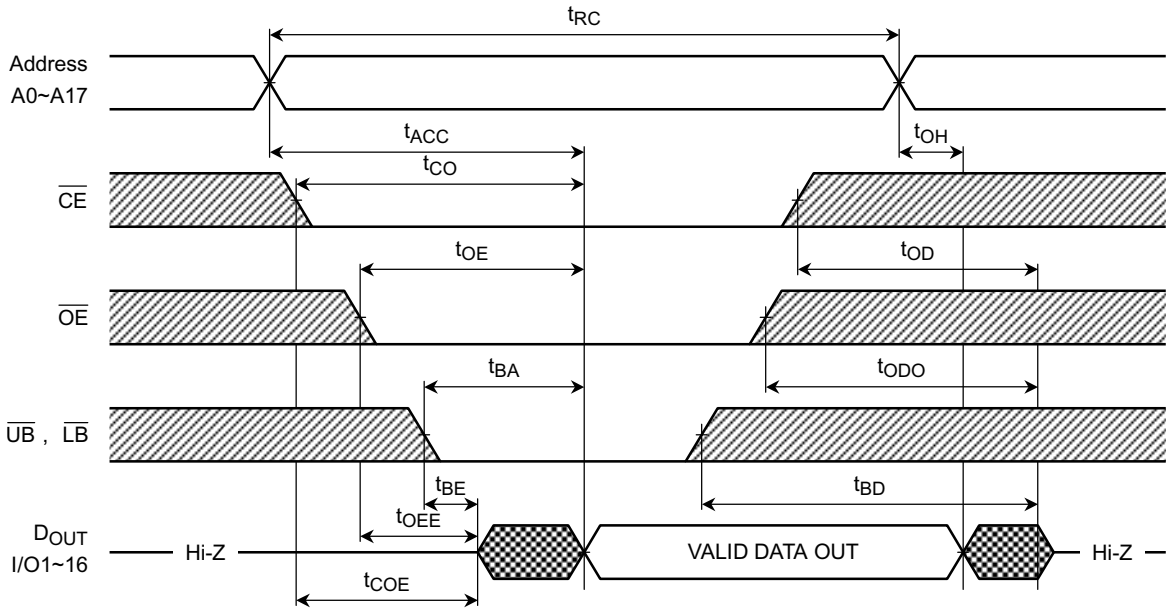
Note: $t_{OD}$, $t_{ODO}$, $t_{BD}$ and $t_{ODW}$ are specified in time when an output becomes high impedance, and are not judged depending on an output voltage level.

## AC TEST CONDITIONS

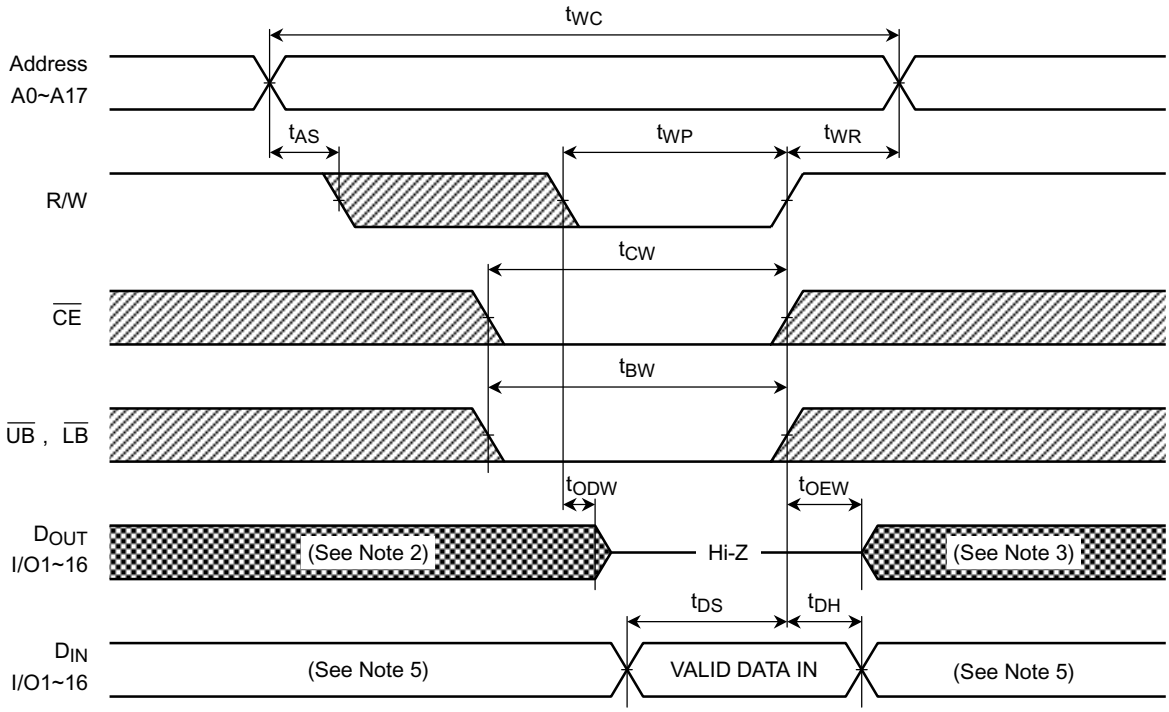
| PARAMETER | TEST CONDITION |
|---|---|
| Input pulse level | 0.4 V, 2.4 V |
| $t_R$, $t_F$ | 5 ns |
| Timing measurements | 1.5 V |
| Reference level | 1.5 V |
| Output load | 100 pF + 1 TTL Gate |

## TIMING DIAGRAMS

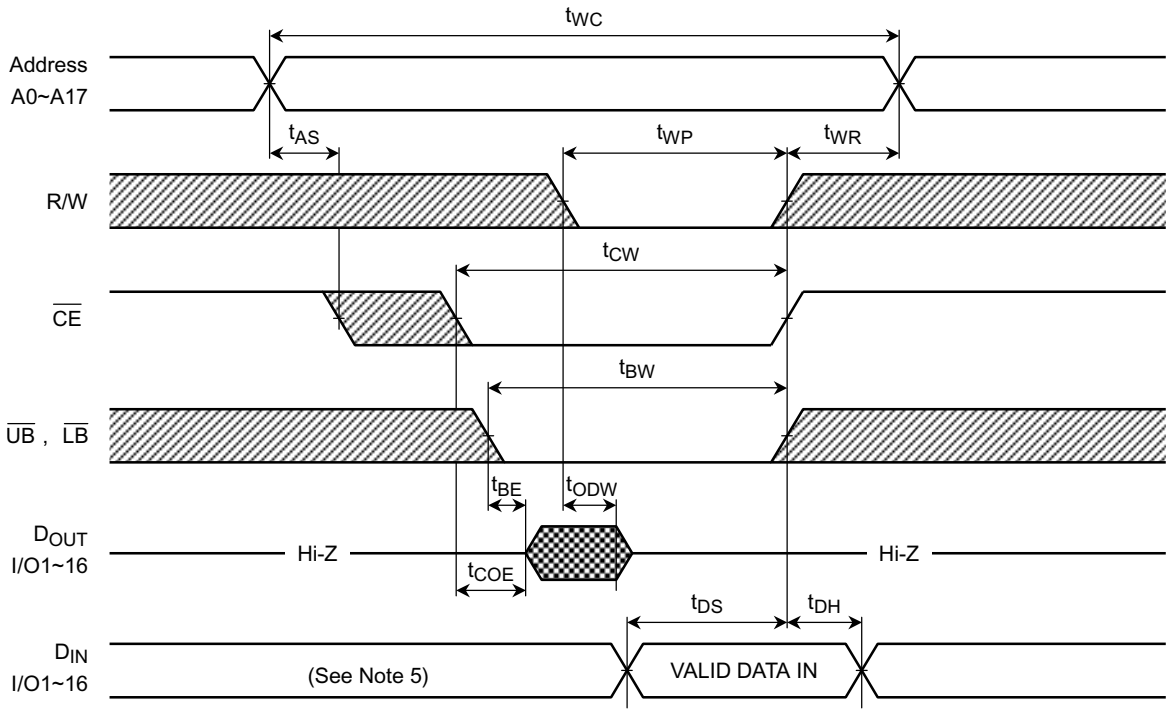
### READ CYCLE (See Note 1)



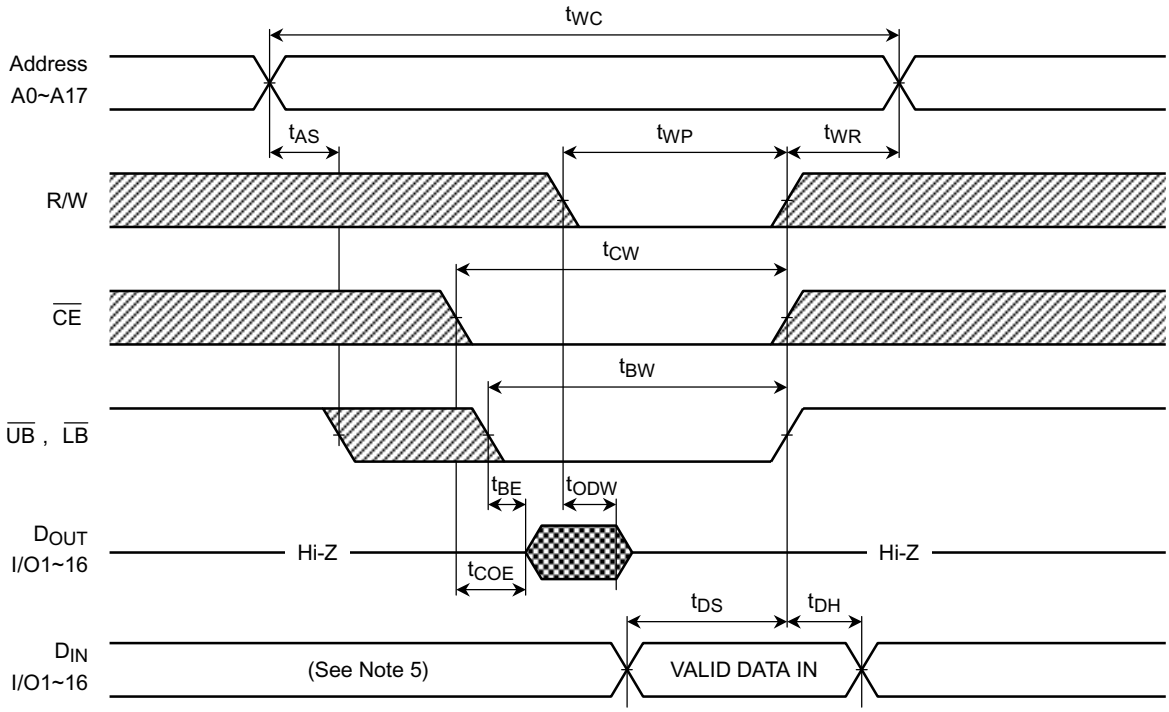

### WRITE CYCLE 1 (R/W CONTROLLED) (See Note 4)



## WRITE CYCLE 2 ( $\overline{CE}$ CONTROLLED) (See Note 4)




## WRITE CYCLE 3 ($\overline{UB}$, $\overline{LB}$ CONTROLLED) (See Note 4)



Note:

(1) R/W remains HIGH for the read cycle.

(2) If $\overline{CE}$ (or $\overline{UB}$ or $\overline{LB}$) goes LOW coincident with or after R/W goes LOW, the outputs will remain at high impedance.

(3) If $\overline{CE}$ (or $\overline{UB}$ or $\overline{LB}$) goes HIGH coincident with or before R/W goes HIGH, the outputs will remain at high impedance.

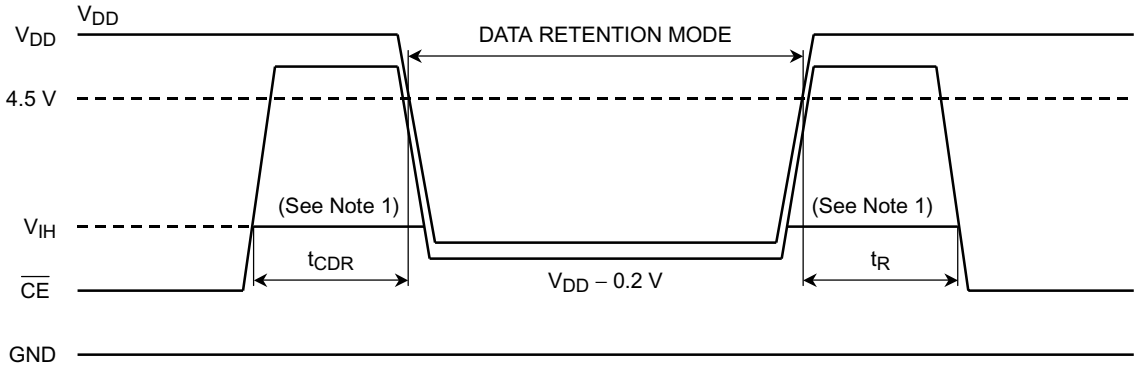
(4) If $\overline{OE}$ is HIGH during the write cycle, the outputs will remain at high impedance.

(5) Because I/O signals may be in the output state at this time, input signals of reverse polarity must not be applied.

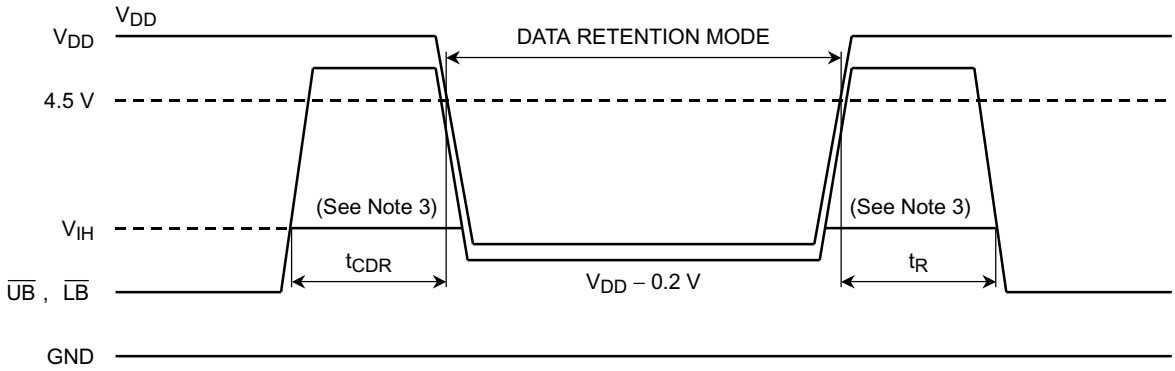
## DATA RETENTION CHARACTERISTICS (Ta = –40° to 85°C)

| SYMBOL | PARAMETER | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{DH}$ | Data Retention Supply Voltage | | 2.0 | — | 5.5 | V |
| $I_{DDS2}$ | Standby Current | Ta = –40~40°C | — | — | 3 | µA |
| | | Ta = –40~85°C | — | — | 20 | |
| $t_{CDR}$ | Chip Deselect to Data Retention Mode Time | | 0 | — | — | ns |
| $t_R$ | Recovery Time | | 5 | — | — | ms |

### $\overline{CE}$ CONTROLLED DATA RETENTION MODE




### $\overline{UB}$, $\overline{LB}$ CONTROLLED DATA RETENTION MODE (See Note 2)



Note:

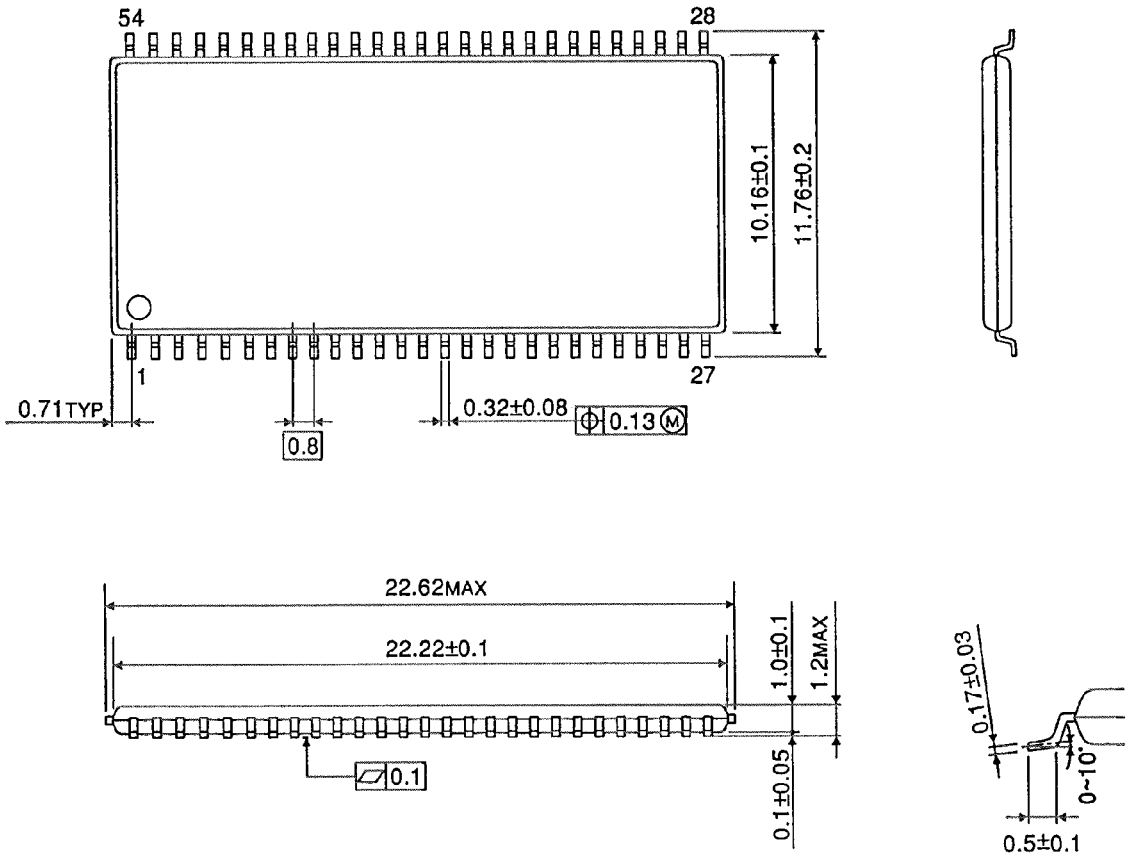
(1) When $\overline{CE}$ is operating at the $V_{IH}$(min.) level(2.2 V), the operating current is given by $I_{DDS1}$ during the transition of $V_{DD}$ from 4.5 to 2.4 V.

(2) In $\overline{UB}$ (or $\overline{LB}$) controlled data retention mode, minimum standby current mode is entered when $\overline{CE} \leq 0.2$ V or $\overline{CE} \geq V_{DD} - 0.2$ V.

(3) When $\overline{UB}$ (or $\overline{LB}$) is operating at the $V_{IH}$(min.) level(2.2 V), the operating current is given by $I_{DDS1}$ during the transition of $V_{DD}$ from 4.5 to 2.4 V.

## PACKAGE DIMENSIONS

TSOPII54-P-400-0.80 Unit: mm




Weight: g (typ)

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